

(Use several sheets if necessary)

**Atty. Docket No.**

**4105-22**

**Applicant**

CHO et al.

Filing Date

**September 10, 2003**

**Serial No.**

**10/658,751**

**TC/A.U.**

2627

[illegible][illegible]

	Cho et al, "Tbit/inch <sup>2</sup> ferroelectric data storage based on scanning nonlinear dielectric microscopy", Applied Physics Letters, Vol. 81, No. 23, December 2, 2002, pages 4401-4403.

Date Considered

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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	2007/0014047	01/2007	Cho et al.			
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\*Examiner

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